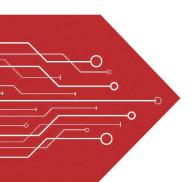
## MSKSEMI















**ESD** 

TVS

**TSS** 

MOV

**GDT** 

**PLED** 

# Broduct data sheet



| Absolute Maximum Ratings | T <sub>A</sub> = 25°C unless otherwise noted |
|--------------------------|--|
|--------------------------|--|

| Symbol           | Parameter                      | Value       | Units |
|------------------|--------------------------------|-------------|-------|
| PD               | Power Dissipation              | 150         | mW    |
| T <sub>STG</sub> | Storage Temperature Range      | -55 to +125 | °C    |
| TJ               | Operating Junction Temperature | +125        | ů     |
| V <sub>R</sub>   | Reverse Voltage                | 85          | ٧     |
| I <sub>FO</sub>  | Forward Current                | 75          | mA    |

These ratings are limiting values above which the serviceability of the diode may be impaired.

#### **FEATURES**

- Fast Switching Speed
- For General Purpose **Switching Applications**
- High Conductance

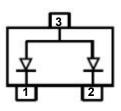
#### **Electrical Symbol & Marking Codes:**



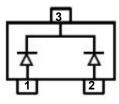
3. Drain



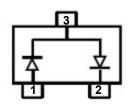
SOT-523



BAW56T-MS Marking: JD



**BAV70T-MS** Marking: JJ



**BAV99T-MS** Marking: JE

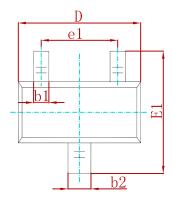
#### **Electrical Characteristics**

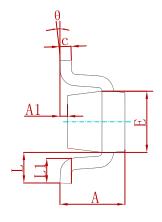
 $T_A$  = 25°C unless otherwise noted

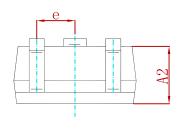
| Symbol           | Parameter                 | Test Condition                         | Limits |         |       | Unit   |  |
|------------------|---------------------------|--|--------|---------|-------|--------|--|
| Symbol           | Parameter                 |  | Min    | Typical | Max   | ] Unit |  |
| V <sub>BR)</sub> | Reverse Breakdown Voltage | I <sub>R</sub> =1µA                    | 85     |         |       | Volts  |  |
| I <sub>R</sub>   | Reverse Leakage Current   | V <sub>R1</sub> =75V                   |        |         | 2     | μА     |  |
|                  |                           | V <sub>R2</sub> =25V                   |        |         | 0.03  |        |  |
| V <sub>F</sub>   | Forward Voltage           | I <sub>F</sub> =1mA                    |        |         | 0.715 |        |  |
|                  |                           | I <sub>F</sub> =10mA                   |        |         | 0.855 | Volts  |  |
|                  |                           | I <sub>F</sub> =50mA                   |        |         | 1.00  |        |  |
|                  |                           | I <sub>F</sub> =150mA                  |        |         | 1.25  |        |  |
| C <sub>D</sub>   | Diode Capacitance         | V <sub>R</sub> =0V, f=1MHz             |        | 1.5     | 4     | pF     |  |
| Trr              | Reverse Recovery Time     | I <sub>F</sub> = I <sub>R</sub> = 10mA |        |         |       |        |  |
|                  |                           | I <sub>RR</sub> =0.1x                  |        |         | 4     | ns     |  |
|                  |                           | $I_{R,R_L}=100\Omega$                  |        |         |       |        |  |



#### **PACKAGE MECHANICAL DATA**

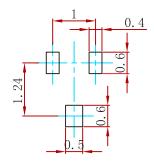






| Cumbal | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
| Symbol | Min.                      | Max.  | Min.                 | Max.  |
| Α      | 0.700                     | 0.900 | 0.028                | 0.035 |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2     | 0.700                     | 0.800 | 0.028                | 0.031 |
| b1     | 0.150                     | 0.250 | 0.006                | 0.010 |
| b2     | 0.250                     | 0.350 | 0.010                | 0.014 |
| С      | 0.100                     | 0.200 | 0.004                | 0.008 |
| D      | 1.500                     | 1.700 | 0.059                | 0.067 |
| Е      | 0.700                     | 0.900 | 0.028                | 0.035 |
| E1     | 1.450                     | 1.750 | 0.057                | 0.069 |
| е      | 0.500 TYP.                |       | 0.020 TYP.           |       |
| e1     | 0.900                     | 1.100 | 0.035                | 0.043 |
| L      | 0.400 REF.                |       | 0.016 REF.           |       |
| L1     | 0.260                     | 0.460 | 0.010                | 0.018 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters. 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

| P/N       | PKG     | QTY  |
|-----------|---------|------|
| BAXXXT-MS | SOT-523 | 3000 |



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